



**Features** 

#### 65V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

100% Unclamped Inductive Switching (UIS) Test in Production —

Ensures More Reliable and Robust End Application

Lead-Free Finish; RoHS Compliant (Notes 1 & 2) Halogen and Antimony Free. "Green" Device (Note 3) For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

Low RDS(ON) — Minimizes Power Losses Low Q<sub>a</sub> — Minimizes Switching Losses Wettable Flank for Improved Optical Inspection

High Conversion Efficiency

Fast Switching Speed Low Input Capacitance

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
65V	4.4mΩ @ V <sub>GS</sub> = 10V	81.7A
	6.3mΩ @ V <sub>GS</sub> = 4.5V	68.2A

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- High Frequency Switching
- Sync Rectification
- DC-DC Converters

# **Description and Applications**

**Mechanical Data** 

- Case: PowerDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0

https://www.diodes.com/quality/product-definitions/

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

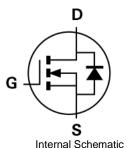


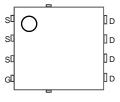
PowerDI5060-8 (SWP) (Type UX)

Top View



**Bottom View** 





Top View Pin Configuration

### **Ordering Information** (Note 4)

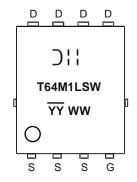
Part Number	Case	Packaging
DMT64M1LPSW-13	PowerDI5060-8 (SWP) (Type UX)	2500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**

#### PowerDI5060-8 (SWP) (Type UX)



);; = Manufacturer's Marking T64M1LSW = Product Type Marking Code YYWW = Date Code Marking  $\overline{YY}$  = Year (ex: 20 = 2020) WW = Week (01 to 53)



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		VDSS	65	V
Gate-Source Voltage		$V_{GSS}$	±20	V
Continuous Drain Comment (Note 5)	T <sub>A</sub> = +25°C	ID	21.8	- A
Continuous Drain Current (Note 5)	T <sub>A</sub> = +70°C		17.5	
Continuous Prain Current (Note 6)	Tc = +25°C	- I <sub>D</sub>	81.7	A
Continuous Drain Current (Note 6)	T <sub>C</sub> = +70°C		65.3	
Maximum Continuous Body Diode Forward Current (Note 6)		Is	80	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	320	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		Ism	320	Α
Avalanche Current, L=1mH		las	20.3	Α
Avalanche Energy, L=1mH		Eas	206	mJ
$V_{DS}$ Spike $t = 10 \mu s$		V <sub>SPIKE</sub>	65	V

#### **Thermal Characteristics**

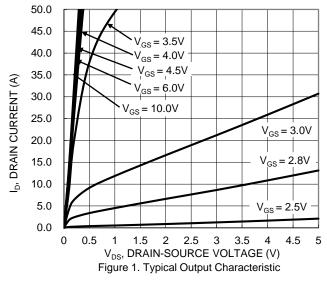
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5) $T_A = +25^{\circ}C$		PD	3.14	W
Thermal Resistance, Junction to Ambient (Note 5)	RθJA	39.8	°C/W	
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		$P_{D}$	44	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	2.84	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

# Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	65	_	_	V	Vgs = 0V, ID = 10mA	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V <sub>DS</sub> = 52V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.3	1.7	2.5	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance		_	3.4	4.4	mO.	Vgs = 10V, ID = 30A	
Static Dialii-Source Ori-Resistance	RDS(ON)	_	4.9	6.3	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 25A	
Diode Forward Voltage	V <sub>SD</sub>	_	8.0	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	2626	_		V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss		905	_	pF		
Reverse Transfer Capacitance	Crss	_	91	_			
Gate Resistance	Rg	_	1.21	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	51.4	_			
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	28.9	_	~C	V <sub>DD</sub> = 30V, I <sub>D</sub> = 30A	
Gate-Source Charge	Qgs	_	8.2	_	nC		
Gate-Drain Charge	Qgd	_	14.4	_			
Turn-On Delay Time	td(ON)	_	11.5	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 30A, R_{G} = 3.3\Omega$	
Turn-On Rise Time	t <sub>R</sub>	_	7.8	_	20		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	35.1	_	ns		
Turn-Off Fall Time	tF	_	19.9	_			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	44.8	_	ns	I- 200 di/dk 4000/	
Body Diode Reverse Recovery Charge	Qrr	_	54.0	_	nC IF = 30A, di/dt = 100A/μs		

 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing. Notes:





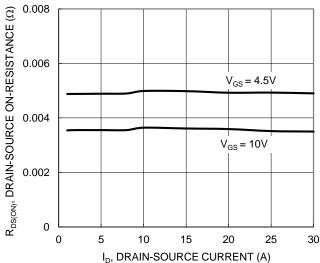


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

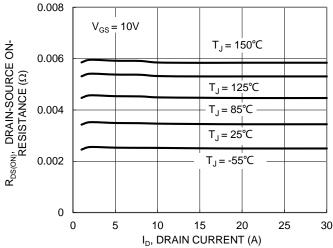


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

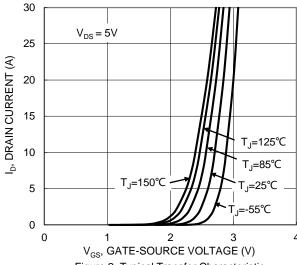


Figure 2. Typical Transfer Characteristic

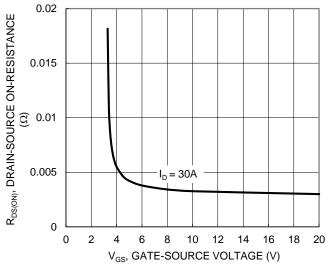
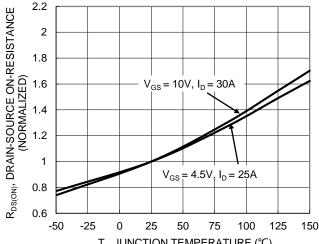


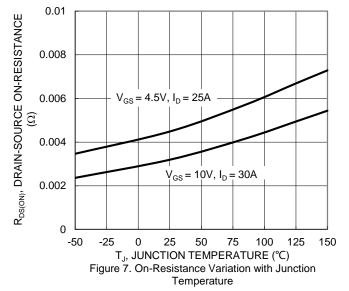
Figure 4. Typical Transfer Characteristic

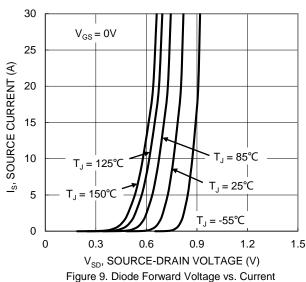


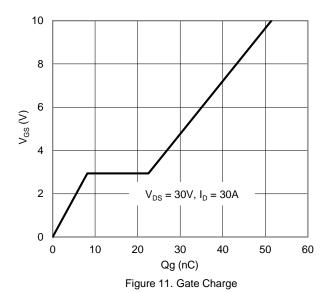
T<sub>J</sub>, JUNCTION TEMPERATURE (°C) Figure 6. On-Resistance Variation with Junction Temperature



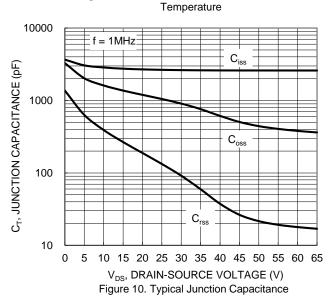


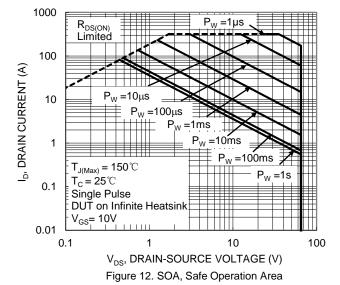






3  $V_{\text{GS}(\text{TH})},$  GATE THRESHOLD VOLTAGE (V) 2.5 2  $I_D = 1 \text{mA}$ 1.5  $I_{D} = 250 \mu A$ 1 0.5 0 -50 -25 0 25 50 75 100 125 150 T<sub>J</sub>, JUNCTION TEMPERATURE (°C) Figure 8. Gate Threshold Variation vs. Junction







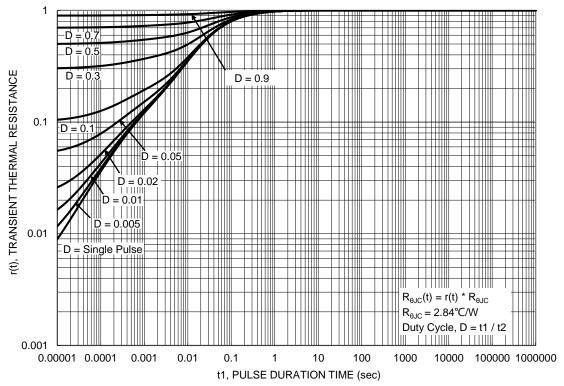


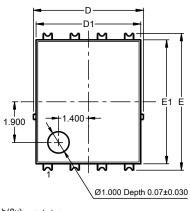
Figure 13. Transient Thermal Resistance

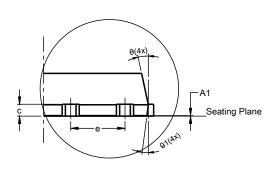


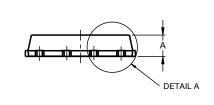
# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (SWP) (Type UX)







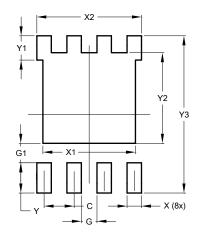
DETAIL A

PowerDI5060-8 (SWP)						
(Type UX)						
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0	0.05				
b	0.30	0.50	0.41			
b2	0.20	0.35	0.25			
b4		).25REF	-			
С	0.230	0.330	0.277			
D		.15 BS0	3			
D1	4.70	5.10	4.90			
D2	3.56	3.96	3.76			
D2a	3.78 4.18		3.98			
Е	6.40 BSC					
E1	5.60	6.00	5.80			
E2	3.46	3.86	3.66			
E2a	4.195	4.595	4.395			
е	1.27BSC					
k	1.05					
L	0.635	0.835	0.735			
La	0.635	0.835	0.735			
L1	0.200	0.400	0.300			
L1a	0.050REF					
L4	0.025	0.225	0.125			
M	3.205	4.005	3.605			
θ	10°	12°	11°			
θ1	6°	8°	7°			
All Dimensions in mm						

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (SWP) (Type UX)



Dimensions	Value		
פווטופווסוטווס	(in mm)		
C	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	4.100		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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